Digital transistor (built-in resistors) Driver (60V, 2A) DTDS14GP

Features

1) High hee.

 $h_{FE} = 1500 \text{ (Typ.) (Vce/lc} = 5V/1A)$

2) Low VCE(sat).

 $V_{CE(sat)} = 0.16V (Typ.)$

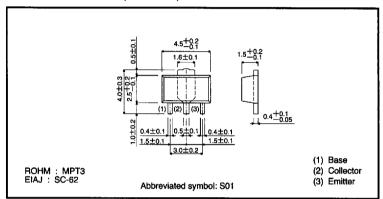
(Ic/IB = 1A/10mA)

 Built-in zener diode for strong protection against reverse surges due to low loads.

Structure

NPN digital transistor (Built-in resistor type)

External dimensions (Units: mm)

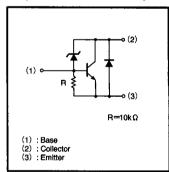


●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	Vсво	60±10	٧	
Collector-emitter voltage	VCEO	60±10	٧	
Emitter-base voltage	VEBO	10	٧	
Collector curren	lc	2	Α	
	ICP	4	A(Pulse)	*1
Base current	Ів	0.03	Α	
Collector power dissipation	Б	0.5	144	
	Pc	2	W	*2
Junction temperature	Tj	150	Ĉ	
Storage temperature	Tstg	−55 ~150	౮	

- *1 Pw≤10ms, Duty≤1/2
- *2 On 40 x 40 x 0.7 mm ceramic board.

Equivalent circuit



Digital transistors

(96-380-DS14GP)

Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage	ВУсво	50		70	٧	Ic=50 μA	
Collector-emitter breakdown voltage	BVcEo	50	_	70	V	lc=50 μA	
Collector cutoff current	Ісво		_	0.5	μΑ	V _{CB} =40V	
Emitter cutoff current	ІЕВО	0.77	_	1.43	mA	V _{EB} =10V	
Collector-emitter saturation voltage	VCE(sat)	_	_	0.3	V	Ic/Is=1A/10mA	
		700	_			VcE=5V, Ic=200mA	*1
DC current transfer ratio	hre	1000	_	_	_	VcE=5V, lc=1A	*1
		500	_	-	_	VcE=5V, Ic=2A	*1
Transition frequency	fr	_	300	_	MHz	VcE=5V, IE=-0.5A, f=100MHz	*2
Emitter-base resistance	R	7	10	13	kΩ	_	
Diode forward voltage	VF			1.5	V	I==1.0A	

^{*1} Measured using pulse current.

Packaging specifications

Туре	Package	МРТ3	
	Package style	Taping	
	Code	T100	
	Basic ordering unit (pieces)	1000	
DTDS14GP		0	

Electrical characteristic curves

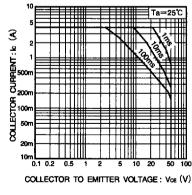


Fig.1 Safe operating area

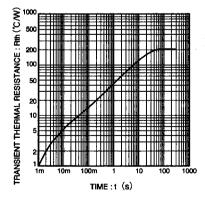


Fig.2 Transient thermal resistance

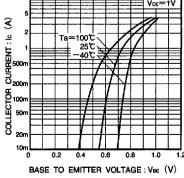


Fig.3 Grounded emitter propagation characteristics

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^{*2} Transition frequency of mounted transistor.

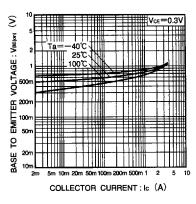


Fig.4 Grounded emitter propagation characteristics

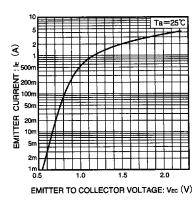


Fig.5 Emitter-collector diode forward characteristics

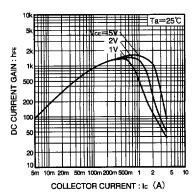


Fig.6 DC current gain vs. collector current (I)

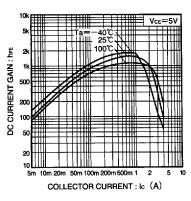


Fig.7 DC current gain vs. collecto rcurrent (II)

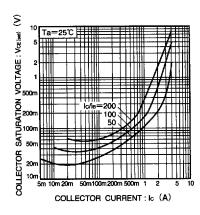


Fig.8 Collector-emitter saturation voltage vs. collector current (I)

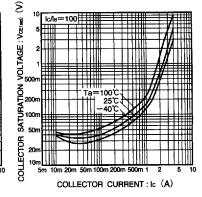


Fig.9 Collector-emitter saturation voltage vs. collector current (II)

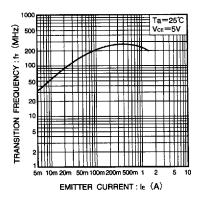


Fig.10 Gain bandwidth product vs. emitter current

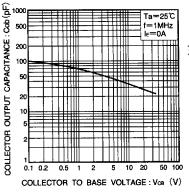


Fig.11 Collector output capacitance vs. collector-base voltage

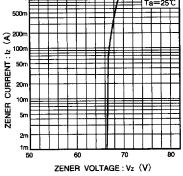
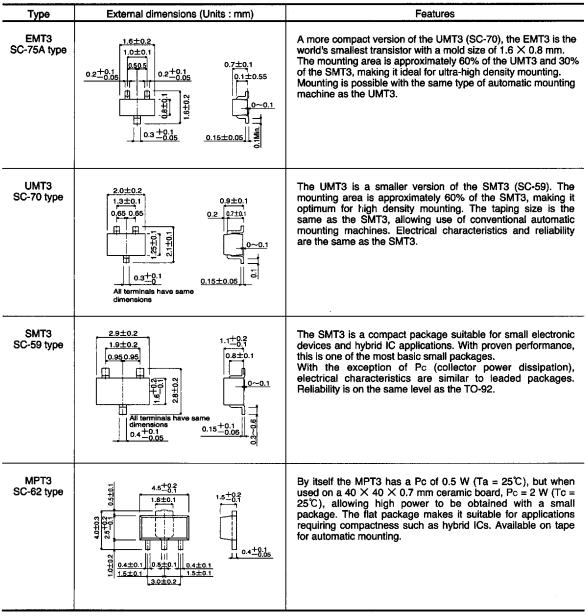


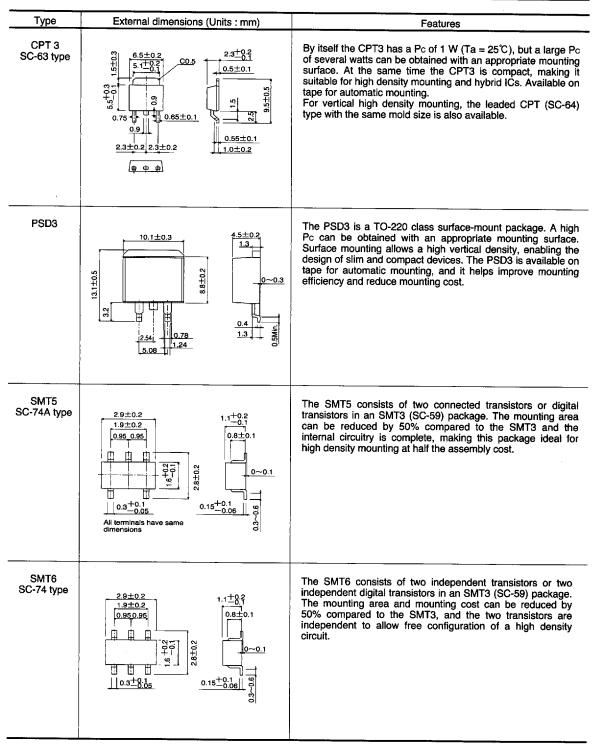
Fig.12 Zener characteristics

Packages

ROHM has been manufacturing transistors since 1975. In the development of products, we constantly strive to anticipate the needs of our customers. Regarding packages, the demands of the market for compactness, low power consumption, low power dissipation and automatic mounting support are becoming ever greater, and we are strengthening our product development system to meet these needs.

Types and features of surface-mount packages

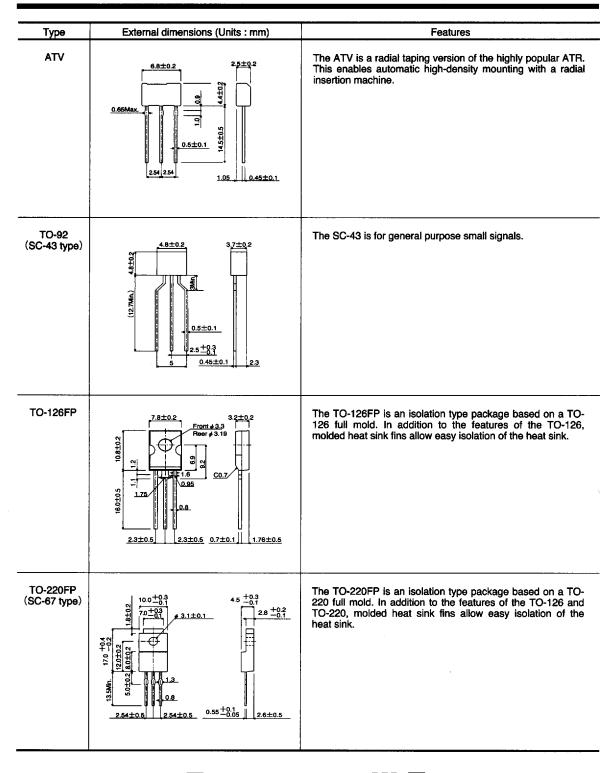




Туре	External dimensions (Units : mm)	Features
UMT5 SC-88A type	2.0±0.2 1,3±0.1 0,85 0,85 0,7 0,005 All terminals have same dimensions	The UMT5 consists of two connected transistors or digital transistors in a UMT3 (SC-70) package. The mounting area can be reduced by 50% compared to the UMT3 and the internal circuitry is completed, making this package ideal for high density mounting at half the assembly cost.
UMT6 SC-88 type	2.0±0.2 1,3±0.1 0.65 0.65 0.7 0.7 0.7 0.7 0.7 0.7 0.7 0.7	The UMT6 consists of two independent transistors or two independent digital transistors in a UMT (SC-70) package. The mounting area and mounting cost can be reduced by 50% compared to the UMT3, and the two transistors are independent to allow free configuration of a high density circuit.

●Types and features of leaded packages

Туре	External dimensions (Units : mm)	Features
SPT (SC-72 type)	2±0,2 0.45±0.15 0.45±0.15 0.5 0.45±0.15 0.5 0.45±0.15	The SPT is a smaller version of the conventional TO-92 type. The body size (3×4×2 mm³) has been reduced to 1/4 that of the TO-92 (5×5×4 mm³). The SPT is available on tape for automatic insertion, and less space is occupied on the printed circuit board than the TO-92. Reliability is the same as the TO-92.
FTR	0.65±0.1 2.4±0.2 0.55±0.1 0.55±0.1 0.45±0.1 0.45±0.1	SIL type with a height of 3.4 mm and a lead pitch of 2.54 mm.
FTL	0.65Max 2.4±0.2 0.65Max 2.4±0.2 0.5±0.1 0.5±0.1	The FTL is a radial taping version of the highly popular FTR. This enables automatic high-density mounting with a radial insertion machine.
ATR (SC-71 type)	0.65Max	SC-71type with a height of 4.4 mm and a Pc=1W type.



Type	External dimensions (Units : mm)	Features
TO-220FN	\$3.2±0.2	The TO-220FN features the same performance as the TO-220FP with approximately 2 mm less height, allowing the design of slimmer devices. Furthermore, the elimination of support pins in the fin (collector electrode) solves short-circuiting problems with neighboring components and the chassis. To make the height to the installation hole the same as the TO-220FP, it can be replaced as is from the TO-220FP.